

<b>Interview Summary</b>	Application No.	Applicant(s)
	09/768,556	INOUE, YUKIHIRO
	Examiner Samuel A Gebremariam	Art Unit 2811

All participants (applicant, applicant's representative, PTO personnel):

(1) Samuel A Gebremariam.

(3) David Ward.

(2) Eddie Lee.

(4) \_\_\_\_\_

Date of Interview: 25 May 2004.

Type: a) Telephonic b) Video Conference  
c) Personal [copy given to: 1) applicant 2) applicant's representative]

Exhibit shown or demonstration conducted: d) Yes e) No.

If Yes, brief description: \_\_\_\_\_

Claim(s) discussed: 13 and 14.

Identification of prior art discussed: Pfiester and admitted prior art.

Agreement with respect to the claims f) was reached. g) was not reached. h) N/A.

Substance of Interview including description of the general nature of what was agreed to if an agreement was reached, or any other comments: See Continuation Sheet.

(A fuller description, if necessary, and a copy of the amendments which the examiner agreed would render the claims allowable, if available, must be attached. Also, where no copy of the amendments that would render the claims allowable is available, a summary thereof must be attached.)

THE FORMAL WRITTEN REPLY TO THE LAST OFFICE ACTION MUST INCLUDE THE SUBSTANCE OF THE INTERVIEW. (See MPEP Section 713.04). If a reply to the last Office action has already been filed, APPLICANT IS GIVEN ONE MONTH FROM THIS INTERVIEW DATE, OR THE MAILING DATE OF THIS INTERVIEW SUMMARY FORM, WHICHEVER IS LATER, TO FILE A STATEMENT OF THE SUBSTANCE OF THE INTERVIEW. See Summary of Record of Interview requirements on reverse side or on attached sheet.

Examiner Note: You must sign this form unless it is an Attachment to a signed Office action.



Examiner's signature, if required

Continuation of Substance of Interview including description of the general nature of what was agreed to if an agreement was reached, or any other comments: Applicant argued that the combined reference of Pfeister and admitted prior art does not teach the claimed limitation of source and drain side offset diffusion such that both ends of the gate insulator form protruding portions that are substantially perpendicular to a direction from the source side offset diffusion layer to the drain side offset diffusion layer. This argument as well as any additional argument will be fully considered in the response to the last office action.